

N-channel 30 V 1.0 m $\Omega$  logic level MOSFET in D2PAK 2 April 2014

**Product data sheet** 

#### 1. **General description**

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### **Features and benefits** 2.

- High efficiency due to low switching and conduction losses •
- Suitable for logic level gate drive sources

#### **Applications** 3.

- DC-to-DC converters •
- Load switiching
- Motor control
- Server power supplies

#### **Quick reference data** 4.

uick reference data						
Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	-	120	А
total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	306	W
junction temperature			-55	-	175	°C
cteristics					_	
drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		-	0.89	1	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13; Fig. 12		-	1.19	1.5	mΩ
aracteristics		-				
gate-drain charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 75 A; V <sub>DS</sub> = 15 V;		-	37	-	nC
total gate charge	<u>Fig. 14; Fig. 15</u>		-	118	-	nC
	Parameter   drain-source voltage   drain current   total power dissipation   junction temperature   cteristics   drain-source on-state   resistance   gate-drain charge	ParameterConditionsdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $T_{mb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; Fig. 2$ total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ junction temperature $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ cteristicsdrain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 25 \ ^{\circ}C; Fig. 12$ $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 100 \ ^{\circ}C; Fig. 13; Fig. 12$ aracteristicsgate-drain charge $V_{GS} = 4.5 \ V; \ I_D = 75 \ A; \ V_{DS} = 15 \ V; Fig. 14; Fig. 15$	ParameterConditionsdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $T_{mb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; Fig. 2$ total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ junction temperature $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ total resistance $V_{GS} = 10 \ V; I_D = 25 \ A; T_j = 25 \ ^{\circ}C; Fig. 12$ drain-source on-state resistance $V_{GS} = 10 \ V; I_D = 25 \ A; T_j = 100 \ ^{\circ}C; Fig. 12$ $V_{GS} = 10 \ V; I_D = 25 \ A; T_j = 100 \ ^{\circ}C; Fig. 13; Fig. 12$ aracteristicsgate-drain charge $V_{GS} = 4.5 \ V; I_D = 75 \ A; V_{DS} = 15 \ V; Fig. 14; Fig. 15$	ParameterConditionsMindrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ -drain current $T_{mb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; Fig. 2$ [1]total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 1$ -junction temperature-55cteristicsdrain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 25 \ ^{\circ}C; Fig. 12$ $V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 100 \ ^{\circ}C; Fig. 12; V_{GS} = 10 \ V; \ I_D = 25 \ A; \ T_j = 100 \ ^{\circ}C; Fig. 13; Fig. 12-aracteristicsgate-drain chargeV_{GS} = 4.5 \ V; \ I_D = 75 \ A; \ V_{DS} = 15 \ V; I_D = 15 \ V; $	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 ^{\circ}C; T_j \le 175 ^{\circ}C$ drain current $T_{mb} = 25 ^{\circ}C; V_{GS} = 10  V; Fig. 2$ [1]-total power dissipation $T_{mb} = 25 ^{\circ}C; Fig. 1$ junction temperature-55-drain-source on-state resistance $V_{GS} = 10  V;  I_D = 25  A;  T_j = 25 ^{\circ}C;$ Fig. 12-0.89 $V_{GS} = 10  V;  I_D = 25  A;  T_j = 100 ^{\circ}C;$ Fig. 13; Fig. 12-1.19aracteristicsgate-drain charge $V_{GS} = 4.5  V;  I_D = 75  A;  V_{DS} = 15  V;$ -37	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 ^\circ$ C; $T_j \le 175 ^\circ$ C30drain current $T_{mb} = 25 ^\circ$ C; $V_{GS} = 10 $ V; Fig. 2[1]120total power dissipation $T_{mb} = 25 ^\circ$ C; Fig. 1306junction temperature-55-175cteristicsdrain-source on-state resistance $V_{GS} = 10 $ V; $I_D = 25 $ A; $T_j = 25 ^\circ$ C; Fig. 12-0.891 $V_{GS} = 10 $ V; $I_D = 25 $ A; $T_j = 100 ^\circ$ C; Fig. 13; Fig. 12-1.191.5aracteristicsgate-drain charge $V_{GS} = 4.5 $ V; $I_D = 75 $ A; $V_{DS} = 15 $ V; Fig. 15-37-

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### N-channel 30 V 1.0 m $\Omega$ logic level MOSFET in D2PAK

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							-
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped		-	-	1.9	J

[1] Continuous current is limited by package.

#### **Pinning information** 5.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UTA
mb	D	mounting base; connected to drain		mbb076 S
			D2PAK (SOT404)	

[1] It is not possible to make connection to pin 2

#### **Ordering information** 6.

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PSMNR90-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404					

#### Marking 7.

Table 4. Marking codes	
Type number	Marking code
PSMNR90-30BL	PSMNR90-30BL

#### **Limiting values** 8.

#### Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

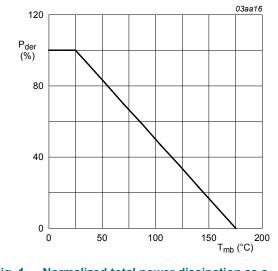
Symbol	Parameter	Conditions	Ν	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	-	30	V
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# PSMNR90-30BL

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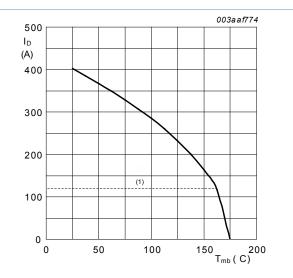
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	306	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	120	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	1573	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	1573	А
Avalanche r	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped		-	1.9	J

[1] Continuous current is limited by package.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

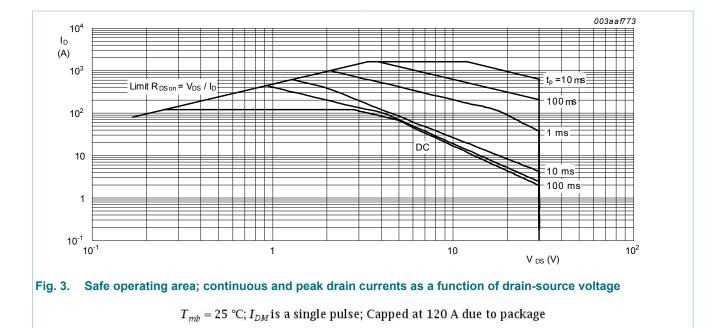


# Fig. 2. Continuous drain current as a function of mounting base temperature.

 $V_{GS} \ge 10 \text{ V}; \quad (1) \text{ Capped at } 120 \text{ A due to package}$ 

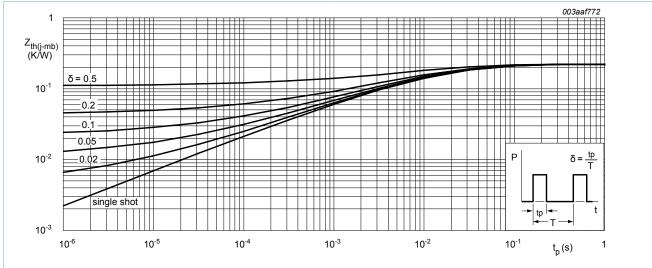
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### N-channel 30 V 1.0 mΩ logic level MOSFET in D2PAK



### 9. Thermal characteristics

Table 6. 1	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.22	0.49	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



# Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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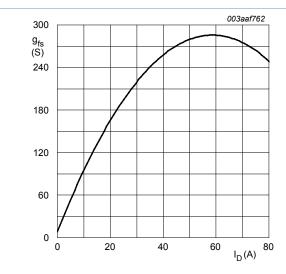
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.3	1.7	2.2	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 11	0.65	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 11	-	-	2.5	V
DSS	drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	10	μA
		$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
GSS	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	-	0.89	1	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	-	1.1	1.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 13; Fig. 12	-	1.65	2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13; Fig. 12	-	1.19	1.5	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	243	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	222	-	nC
		$I_{D}$ = 75 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V;	-	118	-	nC
Q <sub>GS</sub>	gate-source charge	<u>Fig. 14; Fig. 15</u>	-	39	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	22	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	17	-	nC
Q <sub>GD</sub>	gate-drain charge		-	37	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 15 V; <u>Fig. 14; Fig. 15</u>	-	2.8	-	V

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### N-channel 30 V 1.0 m $\Omega$ logic level MOSFET in D2PAK

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 15 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	14850	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	 -	2799	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1215	-	pF
t <sub>d(on)</sub>	turn-on delay time	$\begin{split} V_{DS} &= 15 \text{ V}; \text{ R}_{L} = 0.2 \Omega; \text{ V}_{GS} = 5 \text{ V}; \\ \text{R}_{G(ext)} &= 5 \Omega; \text{ I}_{D} = 75 A; \text{ T}_{j} = 25 ^{\circ}\text{C} \end{split}$	-	95	-	ns
t <sub>r</sub>	rise time	$\begin{split} V_{DS} &= 15 \text{ V}; \text{ R}_{L} = 0.2 \Omega; V_{GS} = 5 V; \\ \text{ R}_{G(ext)} &= 5 \Omega; T_{j} = 25 ^{\circ}\text{C}; I_{D} = 75 A \end{split}$	-	213	-	ns
t <sub>d(off)</sub>	turn-off delay time	$V_{DS}$ = 15 V; R <sub>L</sub> = 0.2 Ω; V <sub>GS</sub> = 5 V;	-	199	-	ns
t <sub>f</sub>	fall time	$R_{G(ext)}$ = 5 $\Omega$ ; $I_D$ = 75 A; $T_j$ = 25 °C	 -	115	-	ns
Source-dra	iin diode	l				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 25 A; dI_{S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	67	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V	-	123	-	nC





 $T_j = 25 \,^{\circ}C; V_{DS} = 15V$ 

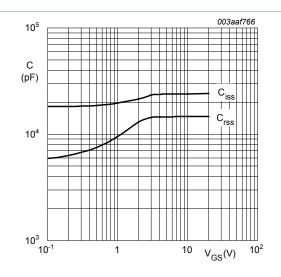
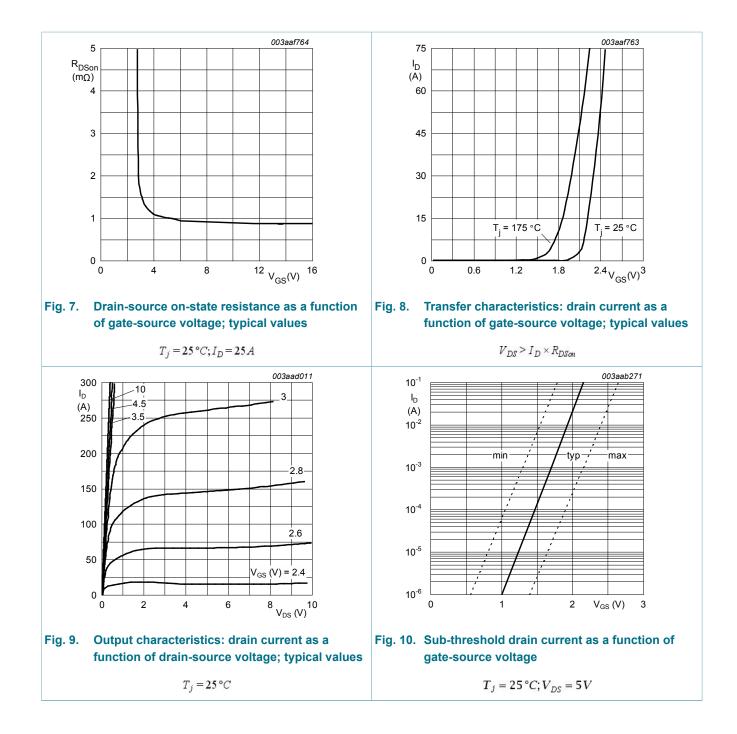


Fig. 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

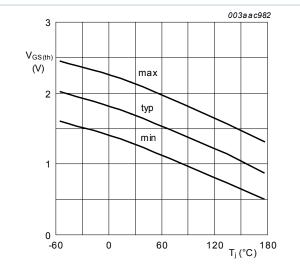
 $V_{DS} = 0V; f = 1MHz$ 

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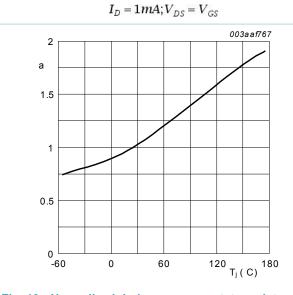
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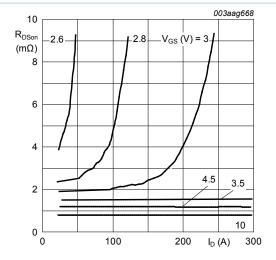








 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$ 





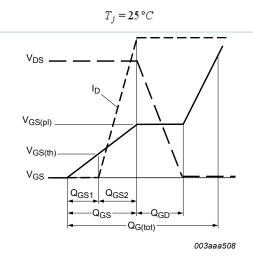
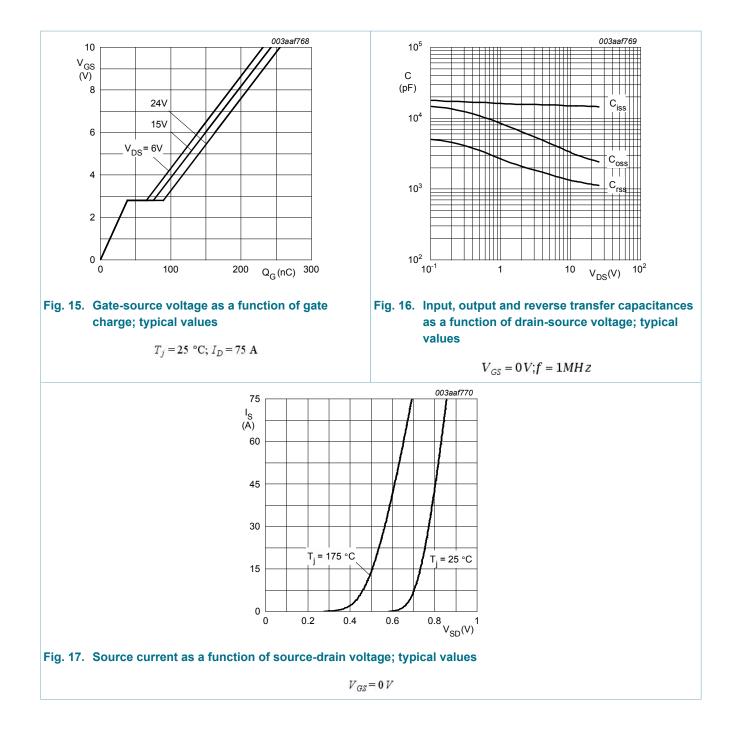


Fig. 14. Gate charge waveform definitions

**Product data sheet** 

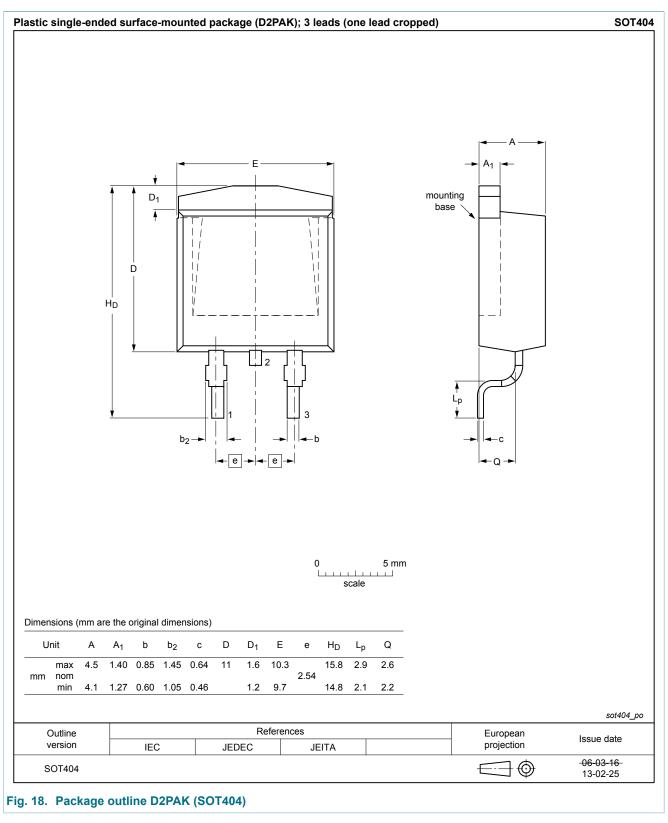
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### N-channel 30 V 1.0 m $\Omega$ logic level MOSFET in D2PAK



#### N-channel 30 V 1.0 m $\Omega$ logic level MOSFET in D2PAK

### 11. Package outline



#### N-channel 30 V 1.0 m $\Omega$ logic level MOSFET in D2PAK

### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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